

# MA3X158

Silicon epitaxial planar type

For small power rectification and surge absorption

### ■ Features

- High reverse voltage  $V_R$
- Large forward current  $I_{F(AV)}$
- Small package and allowing automatic mounting

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

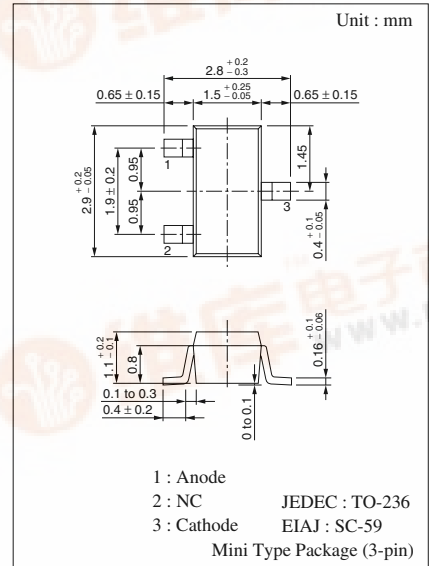
Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	$V_R$	200	V
Repetitive peak reverse voltage	$V_{RRM}$	250	V
Non-repetitive peak forward surge voltage	$V_{RSM}$	300	V
Output current	$I_{F(AV)}$	100	mA
Non-repetitive peak forward surge current*	$I_{FSM}$	500	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +125	$^\circ\text{C}$

Note) \* :  $t = 1\text{ s}$

### ■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse current (DC)	$I_R$	$V_R = 200\text{ V}$			1.0	$\mu\text{A}$
Forward voltage (DC)	$V_F$	$I_F = 100\text{ mA}$			1.3	V

Note) Rated input/output frequency: 3 MHz



Marking Symbol: M1C

Internal Connection

